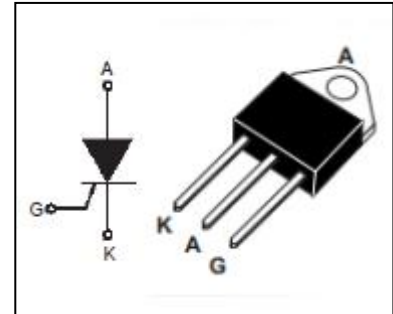


APPLICATIONS

Available in high power packages, BTW69 Series is suitable in applications where power handling and power dissipation are critical, such as solid state relays, welding equipment, high power motor

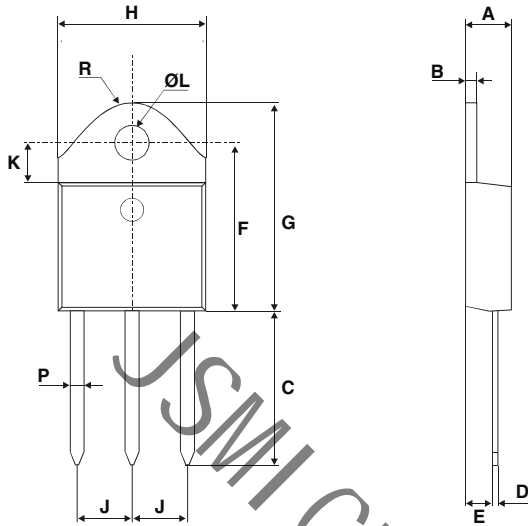
Minimum Lot-to-Lot variations for robust device performance and reliable operation


ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	MIN	UNIT
V _{DRM}	Repetitive peak off-state voltage	1200	V
V _{RRM}	Repetitive peak reverse voltage	1200	V
I _{T(AV)}	Average on-state current , T _c =70° C	31	A
I _{T(RMS)}	RMS on-state current , T _c =70° C	50	A
I _{TSM}	Surge non-repetitive on-state current	T _P =10ms 500	A
P _{G(AV)}	Average gate power dissipation	1	W
T _j	Operating junction temperature	-40~125	°C
T _{stg}	Storage temperature	-40~150	°C

ELECTRICAL CHARACTERISTICS (T_c=25°C unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
I _{RRM}	Repetitive peak reverse current	V _{RM} =V _{RRM}	T _j =25°C	10	μA
			T _j =125°C	5	mA
I _{DRM}	Repetitive peak off-state current	V _{DM} =V _{DRM}	T _j =25°C	10	μA
			T _j =125°C	5	mA
V _{TM}	On-state voltage	I _{TM} = 100A		1.6	V
I _{GT}	Gate-trigger current	V _D = 12 V; R _L = 33 Ω		50	mA
V _{GT}	Gate-trigger voltage	V _D = 12 V; R _L = 33 Ω		1.3	V
R _{th(j-c)}	Thermal resistance	Junction to case		0.45	°C/W

TO-3P (Insulated and non insulated) Package Mechanical Data


REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.4		4.6	0.173		0.181
B	1.45		1.55	0.057		0.061
C	14.35		15.60	0.565		0.614
D	0.5		0.7	0.020		0.028
E	2.7		2.9	0.106		0.114
F	15.8		16.5	0.622		0.650
G	20.4		21.1	0.815		0.831
H	15.1		15.5	0.594		0.610
J	5.4		5.65	0.213		0.222
K	3.4		3.65	0.134		0.144
$\varnothing L$	4.08		4.17	0.161		0.164
P	1.20		1.40	0.047		0.055
R		4.60			0.181	